

Abstract Submitted  
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**Electronic structure of alkali/Si(111):B semiconducting interfaces**

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<sup>1</sup>L. A. Cardenas et al, Phys. Rev. Lett. 103, 046804 (2009)

<sup>2</sup>C. Tournier-Colletta et al., Phys. Rev. B 82, 165429 (2010)

<sup>3</sup>L. Chaput et al., to be published

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